

## **SS9013**

# **1W Output Amplifier of Potable Radios in Class B Push-pull Operation.**

- High total power dissipation. (P<sub>T</sub>=625mW)
- High Collector Current. (I<sub>C</sub>=500mA)
- Complementary to SS9012
- Excellent h<sub>FE</sub> linearity.



1. Emitter 2. Base 3. Collector

# **NPN Epitaxial Silicon Transistor**

### Absolute Maximum Ratings Ta=25°C unless otherwise noted

Symbol	Parameter	Ratings	Units
V <sub>CBO</sub>	Collector-Base Voltage	40	V
V <sub>CEO</sub>	Collector-Emitter Voltage	20	V
V <sub>EBO</sub>	Emitter-Base Voltage	5	V
I <sub>C</sub>	Collector Current	500	mA
P <sub>C</sub>	Collector Power Dissipation	625	mW
T <sub>J</sub>	Junction Temperature	150	°C
T <sub>STG</sub>	Storage Temperature	-55 ~ 150	°C

### Electrical Characteristics T<sub>a</sub>=25°C unless otherwise noted

Symbol	Parameter	Test Condition	Min.	Тур.	Max.	Units
BV <sub>CBO</sub>	Collector-Base Breakdown Voltage	$I_C = 100 \mu A, I_E = 0$	40			V
BV <sub>CEO</sub>	Collector-Emitter Breakdown Voltage	$I_C = 1 \text{mA}, I_B = 0$	20			V
BV <sub>EBO</sub>	Emitter-Base Breakdown Voltage	$I_E = 100 \mu A, I_C = 0$	5			V
I <sub>CBO</sub>	Collector Cut-off Current	$V_{CB} = 25V, I_{E} = 0$			100	nA
I <sub>EBO</sub>	Emitter Cut-off Current	$V_{EB} = 3V$ , $I_C = 0$			100	nA
h <sub>FE1</sub> h <sub>FE2</sub>	DC Current Gain	$V_{CE} = 1V, I_{C} = 50 \text{mA}$ $V_{CE} = 1V, I_{C} = 500 \text{mA}$	64 40	120 120	202	
V <sub>CE</sub> (sat)	Collector-Emitter Saturation Voltage	I <sub>C</sub> =500mA, I <sub>B</sub> =50mA		0.16	0.6	V
V <sub>BE</sub> (sat)	Base-Emitter Saturation Voltage	I <sub>C</sub> =500mA, I <sub>B</sub> =50mA		0.91	1.2	V
V <sub>BE</sub> (on)	Base-Emitter On Voltage	$V_{CE} = 1V$ , $I_{C} = 10mA$	0.6	0.67	0.7	V

# **h**<sub>FE</sub> Classification

Classification	D	E	F	G	Н
h <sub>FE1</sub>	64 ~ 91	78 ~ 112	96 ~ 135	112 ~ 166	144 ~ 202

# **Typical Characteristics**

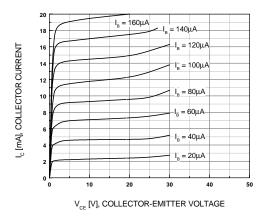


Figure 1. Static Characteristic

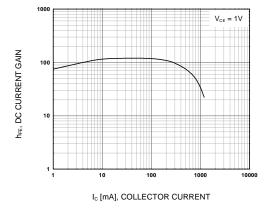


Figure 2. DC current Gain

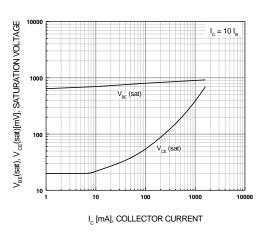


Figure 3. Base-Emitter Saturation Voltage Collector-Emitter Saturation Voltage

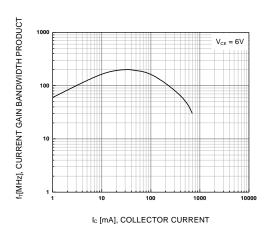
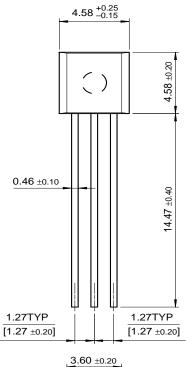
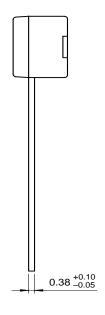


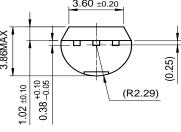
Figure 4. Current Gain Bandwidth Product

# **Package Dimensions**

TO-92







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